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94 9539

Silicon Mesa Rectifier

Features

- Glass passivated junction
- Hermetically sealed package
- Controlled avalanche characteristic
- Low reverse current

Applications

High voltage rectifier

Absolute Maximum Ratings

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Туре	Symbol	Value	Unit
Reverse voltage =Repetitive peak reverse voltage	C.COM		V _R =V _{RRM}	2400	V
Peak forward surge current	t _p =10ms, half sinewave		I _{FSM}	10	А
Average forward current	T _{amb} =25°C, R _{thJA} ≦60K/W		I _{FAV}	350	mA
Non repetitive reverse avalanche energy	I _{(BR)R} =1A, inductive load		E _R	60	mJ
Junction temperature			Ti	175	°C
Storage temperature range		500	T _{stg}	-55+190	°C

Maximum Thermal Resistance

T_i = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	I=10mm, T _L =constant	R _{thJA}	60	K/W

Electrical Characteristics

T_j = 25°C

Parameter	Test Conditions	Туре	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =200mA		V _F	2	DZS	3.0	V
	I _F =1A	1.5	V _F	AL 10 A		3.6	V
	I _F =1A, T _j =175°C	16.10	VF			2.9	V
	$I_{F}=1A, T_{i}=-40^{\circ}C$		V _F			4.0	V
Reverse current	V _R =V _{RRM}		I _R			5	μA
the second second	V _R =V _{RRM} , T _j =175°C		I _R			250	μΑ
WW 2	$V_{R}=V_{RRM}, T_{i}=-40^{\circ}C$		I _R			400	nA
Reverse breakdown voltage	I _R =100μA		V _{(BR)R}	2500			V
Reverse recovery time	I _F =0.5A, I _R =1A, i _R =0.25A		t _{rr}			5	μs

BYT62



Vishay Telefunken

Characteristics ($T_j = 25^{\circ}C$ unless otherwise specified)

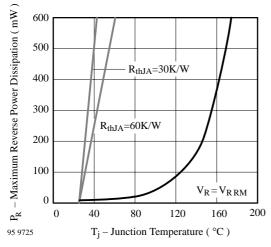


Figure 1. Max. Reverse Power Dissipation vs. Junction Temperature

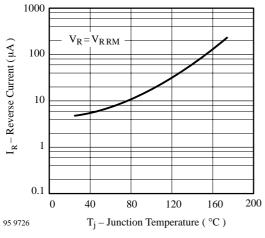
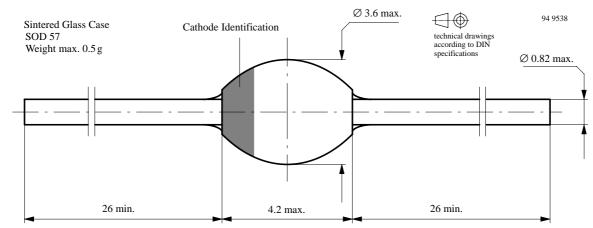
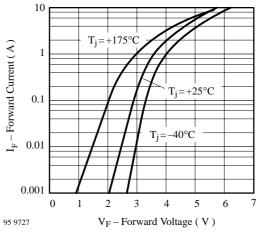


Figure 2. Max. Reverse Current vs. Junction Temperature

Dimensions in mm









BYT62 Vishay Telefunken

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems

with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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